PBSS4160T

60 V, 1 A NPN low VCEsat (BISS) transistor

1 April 2023

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT23 plastic package. PNP complement: PBSS5160T.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency, reduces heat generation
- · Reduces printed-circuit board area required

3. Applications

- Major application segments:
 - · Automotive 42 V power
 - Telecom infrastructure
 - · Industrial.
- · Power management:
 - · DC-to-DC conversion
 - · Supply line switching.
- Peripheral driver
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
I _C	collector current		[1]	-	-	1	Α
I _{CM}	peak collector current	or limited by T _{j(max)} ; t _p = 1 ms		-	-	2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	200	250	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		j
3	С	collector		В — 🛴
				 E
			1 2	sym123
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4160T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4160T	%U5

[1] % = placeholder for manufacturing site code

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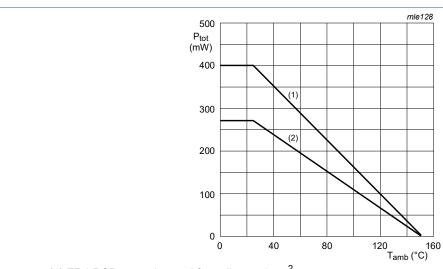
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current		[1]	-	0.9	Α
			[2]	-	1	Α
I _{CM}	peak collector current	or limited by T _{j(max)} ; t _p = 1 ms		-	2	Α
I _B	base current			-	300	mA
I _{BM}	peak base current	$t_p \le 300 \text{ μs; } \delta \le 0.02$		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	270	mW
			[2]	-	400	mW
			[1] [3]	-	1.25	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Pulsed; $t_p \le 10 \text{ ms}$; $\delta \le 0.02$



- (1) FR4 PCB mounting pad for collector 1 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

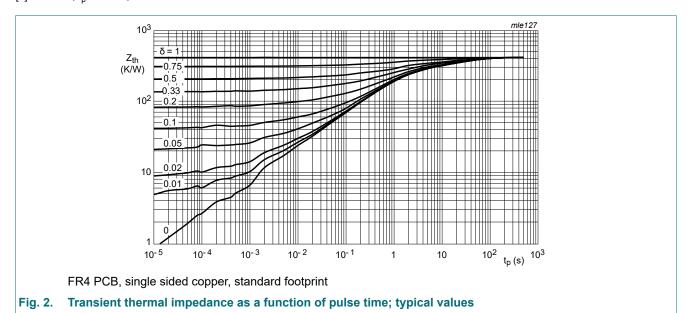
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	_	[1]	-	-	465	K/W	
		[2]	-	-	312	K/W	
			[1] [3]	-	-	100	K/W

- 1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- 2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Pulsed; $t_p \le 10 \text{ ms}$; $\delta \le 0.02$.



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
CU	current	V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 60 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	250	400	-	
		V_{CE} = 5 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	350	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	100	150	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-	90	110	mV
	saturation voltage	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	110	140	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$	-	200	250	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	200	250	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	0.95	1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 5 V; I _C = 1 A; T _{amb} = 25 °C	-	0.82	0.9	V
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	150	220	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	5.5	10	pF

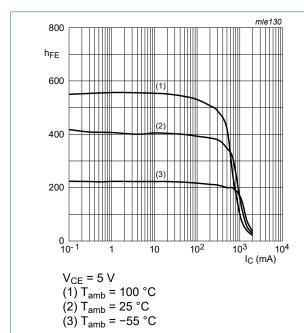


Fig. 3. DC current gain as a function of collector current; typical values

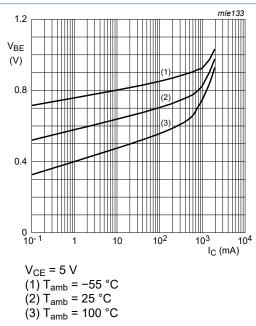


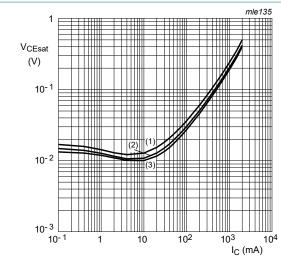
Fig. 4. Base-emitter voltage as a function of collector current; typical values

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$$I_{\rm C}/I_{\rm B} = 10$$

$$I_C/I_B = 10$$

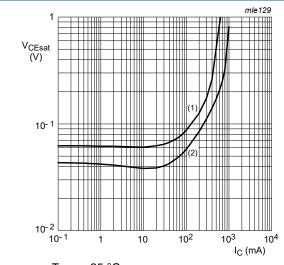
(1) $T_{amb} = 100 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \text{ °C}$$

(3) $T_{amb} = -55 \text{ °C}$

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

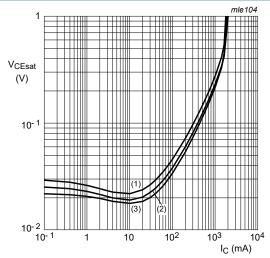


$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



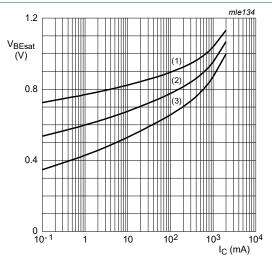
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_C/I_B = 20$$

(1) $T_{amb} = 100 \,^{\circ}C$

(2)
$$T_{amb}$$
= 25 °C
(3) T_{amb} = -55 °C

Fig. 6. Collector-emitter saturation voltage as a function of collector curret; typical values



$$I_{\rm C}/I_{\rm B}=20$$

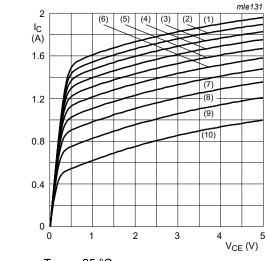
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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 $T_{amb} = 25 \,^{\circ}\text{C}$ (1) $I_B = 60 \,\text{mA}$ (2) $I_B = 54 \,\text{mA}$ (3) $I_B = 48 \,\text{mA}$

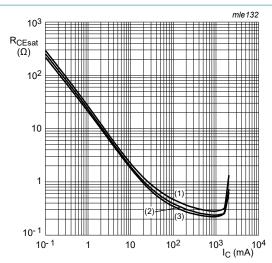
 $(4) I_B = 42 \text{ mA}$ $(5) I_B = 36 \text{ mA}$

 $(6) I_B = 30 \text{ mA}$

 $(7) I_B = 24 \text{ mA}$ $(8) I_B = 18 \text{ mA}$

(9) $I_B = 12 \text{ mA}$ $(10) I_B = 6 \text{ mA}$

Fig. 9. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B}=20$

 $(1) T_{amb} = 100 °C$

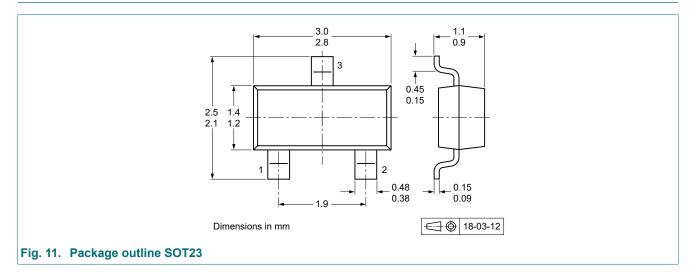
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

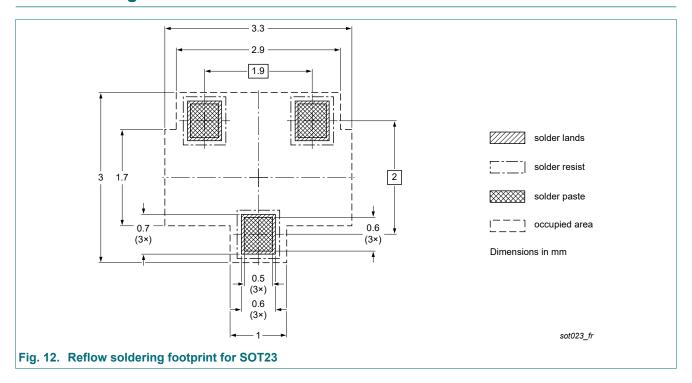
Fig. 10. Equivalent on-resistance as a function of collector current; typical values

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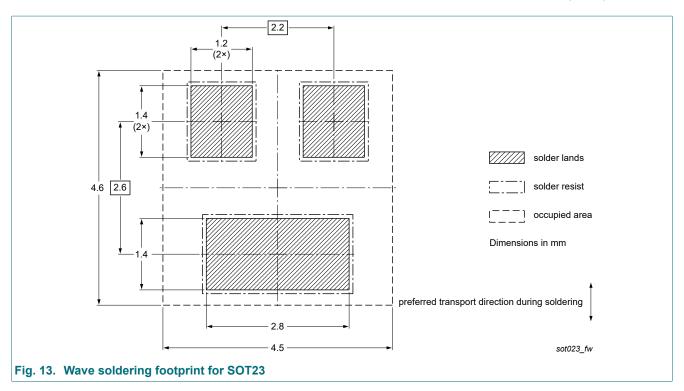
11. Package outline



12. Soldering



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13. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4160T v.3	20230401	Product data sheet	-	PBSS4160T v.2		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Product changed to non automotive. Please refer to the automotive product(s) with -Q. 					
PBSS4160T v.2	20040512	Product data sheet	-	PBSS4160T v.1		
PBSS4160T v.1	20030624	Product specification	-	-		

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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